

EAST - [10726508 vertical sonos.wsp:1]

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((vertical\$2 adj2 (channel transistor tft) pillar) near9 (channel adj length)) and (Oxide adj nitride adj oxide ONO)

Sept 2004

140 (((sonos monos))
18653 common adj source
8 (((sonos monos))
31 (((sonos monos))
168 (((sonos monos)) and (thickness near3 nitride)) and (charge near2 (trap\$4 store
23 (((sonos monos))
2740 sonos
55462 thickness near3 oxide
3119 (thickness near3 nitride) with (thickness near3 oxide)
23 ((thickness near3 nitride) with (thickness near3 oxide)) and sonos
5 (thickness near3 nitride) and (tunnel\$4 near limit)
136 tunnel\$4 near limit
22368 channel adj length
252 (vertical\$2 adj2 (channel transistor tft) pillar) near9 (channel adj length)
4 ((vertical\$2 adj2 (channel transistor tft) pillar) near9 (channel adj length)) and (Ox
28 ((vertical\$2 adj2 (channel transistor tft) pillar) near9 (channel adj length)) and (ch
25 ((vertical\$2 adj2 (channel transistor tft) pillar) near9 (channel adj length)) and (O
1553 (vertical\$2 adj2 (channel transistor tft) pillar) and (channel adj length)
6773994.URPN
28 ("4366495" | "4455565" | "4587713" | "4670768" | "4683643" | "478695

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